What is claimed is :

1.   A mask set for compensating a misalignment between patterns, comprising:

a first mask consisted of a mask substrate on which a main pattern and a plurality of sub-patterns are formed, said sub-patterns formed at a side of said main pattern;

a second mask consisted of a mask substrate on which a plurality of hole patterns are formed, said hole patterns corresponding to spaces between said main pattern and said sub-patterns of said first mask, respectively when said first and second mask are overlapped to each other;

a third mask consisted of mask substrate on which a plurality of bar patterns are formed, said bar patterns corresponding to said hole patterns of said second mask, respectively when said second and third mask are overlapped to each other.

2.   The mask set of claim 1, wherein said plurality of sub-patterns are formed at a predetermined distance with said main pattern.

3.   The mask set of claim 1, wherein said plurality of sub-patterns of said second mask are formed at positions consecutively shifted to both direction by a certain distance basis on the central sub-pattern.

4. The mask set of claim 1, wherein said mask substrates of said first, second, and third masks are made of transparent materials.

5. The mask set of claim 1, wherein said main pattern and said sub-patterns of said first mask and said bar patterns of said third mask are made of light-shielding materials..

6. The mask set of claim 1, wherein said main pattern of said first mask is divided into a first main pattern and a second main pattern at right angle each other.

7. A method of compensating a misalignment between patterns, comprising the steps of:

forming a first test pattern and a plurality of second test patterns on a first insulating layer formed on a test wafer using a first mask;

forming a second insulating layer on said first insulating layer including said first test pattern and said plurality of second test patterns and then forming contact holes between said first test pattern and said plurality of second test patterns, respectively, using a second mask;

forming third test patterns on said plurality of contact holes, respectively, using a third mask;

measuring resistance using a resistance tester of which one terminal is

connected to said first test pattern and another terminal is connected to said plurality of second test patterns one by one; and

confirming a misalignment between the patterns using the measured resistance value.

8. The method of claim 7, wherein said first mask is consisted of a mask substrate on which a main pattern and a plurality of sub-patterns are formed, and said sub-patterns are formed at a side of said main pattern.

9. The method of claim 7, wherein said second mask is consisted of a mask substrate on which a plurality of hole patterns are formed, and said hole patterns correspond to spaces between said main pattern and said sub-patterns of said first mask, respectively when said first and second mask are overlapped to each other.

10. The method of claim 7, wherein said third mask is consisted of mask substrate on which a plurality of bar patterns are formed, said bar patterns are correspond to said hole patterns of said second mask, respectively when said second and third mask are overlapped to each other.

11. The method of claim 8, wherein said plurality of sub-patterns are formed at a predetermined distance with said main pattern.

12.   The method of claim 8, wherein said plurality of sub-patterns of said second mask are formed at positions consecutively shifted to both direction by a certain distance basis on the central sub-pattern.

13.   The mask set of claim 8, wherein said main pattern of said first mask is divided into a first main pattern and a second main pattern at right angle each other.